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provided on the same semiconductor substrate so that the light emitting active layers lie substantially in parallel to a main surface of the semiconductor substrate, and a high-resistance region provided between the semiconductor laser resonators.

16. (Unamended) A semiconductor laser device comprising:  
first and second semiconductor laser resonators provided on the same semiconductor substrate, an active layer of the first laser resonator being of a different material than an active layer of the second laser resonator;  
the active layer of the second laser resonator being provided in a groove, whereas the active layer of the first laser resonator is not provided in a groove; and  
a high-resistance region provided at least along a sidewall of the groove in which the active layer of the second laser resonator is provided, the high-resistance region comprising ions and/or protons implanted into the sidewall of the groove.

**REMARKS**

This is in response to the Office Action dated September 25, 2002. Claims 1-11, 16 and 17 are pending. Attached hereto is a marked-up version of the changes made to the claim(s) by the current amendment. The attached page(s) is captioned "**Version With Markings To Show Changes Made.**"

For purposes of example and without limitation, certain example embodiments of this invention relate to a semiconductor laser device including multiple laser resonators. One laser resonator may emit light at a *first wavelength*, and another resonator may emit